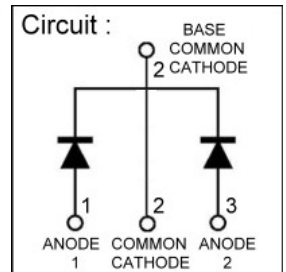
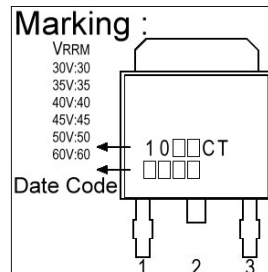
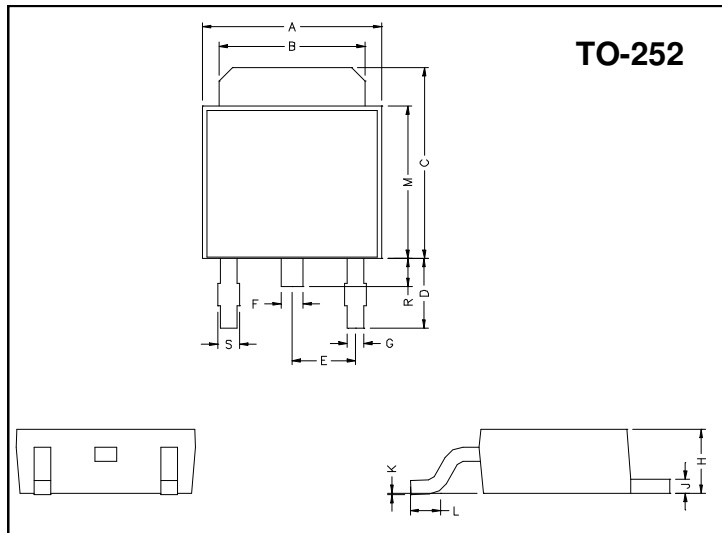


GJSBL1030CT~1060CT**SCHOTTKY BARRIER RECTIFIERS****REVERSE VOLTAGE 30V TO 60V, CURRENT 10A****Description**

The GJSBL1030CT~1060CT are designed for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

Features

- Guard ring for transient protection
- Low power loss, high efficiency
- High current capability, low V_F
- High surge capacity

Package Dimensions

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Maximum Ratings and Electrical Characteristics at $T_a=25^\circ\text{C}$ unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

Parameters	Symbol	Ratings						Unit
		GJSBL 1030CT	GJSBL 1035CT	GJSBL 1040CT	GJSBL 1045CT	GJSBL 1050CT	GJSBL 1060CT	V
Max. Recurrent Peak Reverse Voltage	V_{RRM}	30	35	40	45	50	60	V
Max. RMS Voltage	V_{RMS}	21	24.5	28	31.5	35	42	V
Max. DC Blocking Voltage	V_{DC}	30	35	40	45	50	60	V
Max. Average Forward Rectified Current (See Fig.1) @ $T_C=95^{\circ}C$	$I_{(AV)}$	10						A
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	125						A
Max. Forward Voltage @ 5A (Note 1)	V_F	0.55				0.7		V
Max. DC Reverse Current @ $T_J=25^{\circ}C$ At Rated DC Blocking Voltage @ $T_J=100^{\circ}C$	I_R	0.5 50						mA
Typical Thermal Resistance @ $T_C=25^{\circ}C$ (Note2)	$R_{\theta JC}$	10						$^{\circ}C/W$
Operating Temperature Range	T_j	-55 ~ +125						$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 ~ +150						$^{\circ}C$

Notes: 1. 300us Pulse Width, 2% Duty Cycle.

2. Thermal Resistance Junction to Case.

Characteristics Curve

Fig. 1 Forward Current Derating Curve

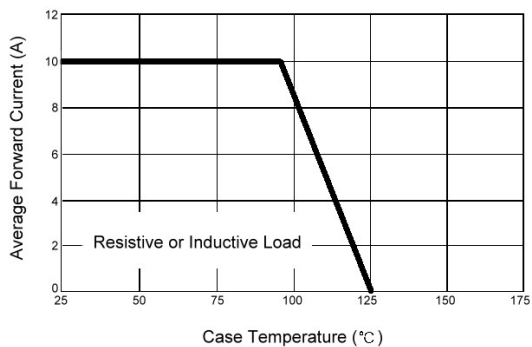


Fig. 2 Maximum Non-Repetitive Surge Current

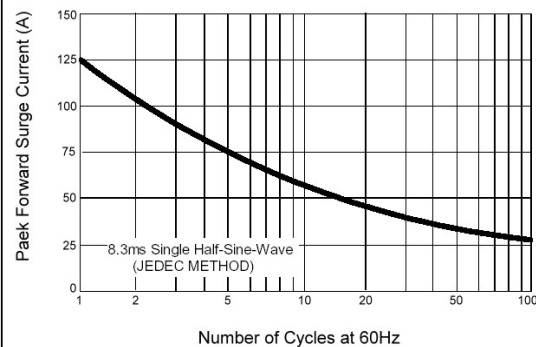


Fig. 3 Typical Reverse Characteristics

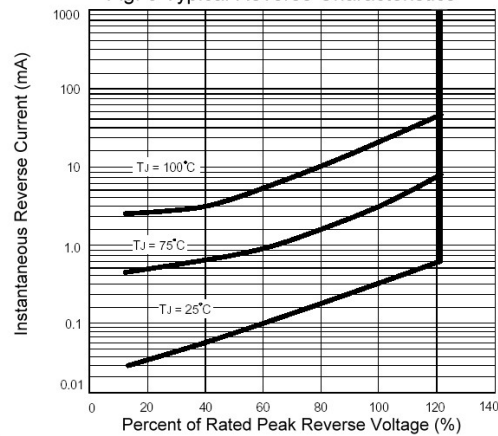


Fig. 4 Typical Forward Characteristics

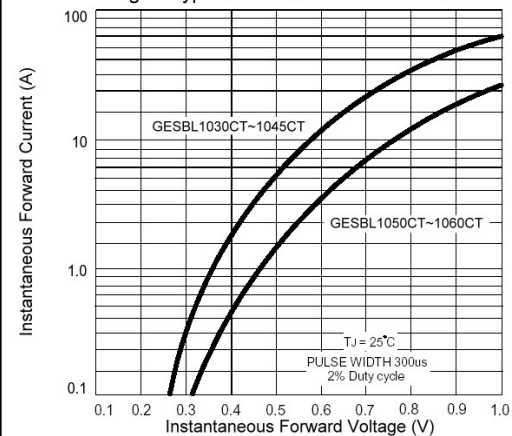
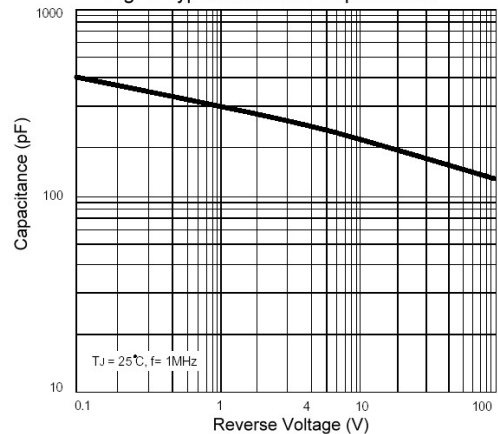


Fig. 5 Typical Junction Capacitance



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